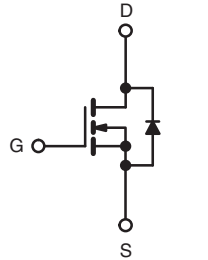
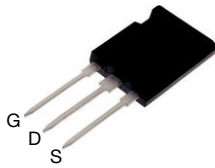


E Series Power MOSFET

| PRODUCT SUMMARY | | |
|---|-----------------|------|
| V_{DS} (V) at T_J max. | 700 | |
| $R_{DS(on)}$ max. at 25 °C (Ω) | $V_{GS} = 10$ V | 0.18 |
| Q_g max. (nC) | 110 | |
| Q_{gs} (nC) | 15 | |
| Q_{gd} (nC) | 32 | |
| Configuration | Single | |

TO-247AD


N-Channel MOSFET

FEATURES

- Low Figure-of-Merit (FOM) $R_{on} \times Q_g$
- Low Input Capacitance (C_{iss})
- Reduced Switching and Conduction Losses
- Ultra Low Gate Charge (Q_g)
- Avalanche Energy Rated (UIS)
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Server and Telecom Power Supplies
- Switch Mode Power Supplies (SMPS)
- Power Factor Correction Power Supplies (PFC)
- Lighting
 - High-Intensity Discharge (HID)
 - Fluorescent Ballast Lighting
- Industrial
 - Welding
 - Induction Heating
 - Motor Drives
 - Battery Chargers
 - Renewable Energy
 - Solar (PV Inverters)

ORDERING INFORMATION

| | |
|---------------------------------|----------------|
| Package | TO-247AD |
| Lead (Pb)-free and Halogen-free | SiHW22N65E-GE3 |


ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

| PARAMETER | SYMBOL | LIMIT | UNIT |
|---|------------------|----------------|------|
| Drain-Source Voltage | V_{DS} | 650 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Gate-Source Voltage AC ($f > 1$ Hz) | | 30 | |
| Continuous Drain Current ($T_J = 150$ °C) | V_{GS} at 10 V | $T_C = 25$ °C | A |
| | | $T_C = 100$ °C | |
| Pulsed Drain Current ^a | I_{DM} | 56 | |
| Linear Derating Factor | | 1.8 | W/°C |
| Single Pulse Avalanche Energy ^b | E_{AS} | 691 | mJ |
| Maximum Power Dissipation | P_D | 227 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to + 150 | °C |
| Drain-Source Voltage Slope | dV/dt | $T_J = 125$ °C | V/ns |
| Reverse Diode dV/dt^d | | 37 | |
| Soldering Recommendations (Peak Temperature) ^c | for 10 s | 26 | °C |
| | | 300 | |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 7$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient | R_{thJA} | - | 62 | °C/W |
| Maximum Junction-to-Case (Drain) | R_{thJC} | - | 0.55 | |

| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | |
|---|---------------------|---|--|------|------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | | 650 | - | - | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$ | | - | 0.74 | - | V/°C |
| Gate-Source Threshold Voltage (N) | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | | 2 | - | 4 | V |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$ | | - | - | 1 | μA |
| | | $V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | | - | - | 10 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ | $I_D = 11\text{ A}$ | - | 0.15 | 0.18 | Ω |
| Forward Transconductance | g_{fs} | $V_{DS} = 8\text{ V}, I_D = 5\text{ A}$ | | - | 6.7 | - | S |
| Dynamic | | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$ | | - | 2415 | - | μF |
| Output Capacitance | C_{oss} | | | - | 118 | - | |
| Reverse Transfer Capacitance | C_{rss} | | | - | 4 | - | |
| Effective Output Capacitance, Energy Related ^a | $C_{o(er)}$ | $V_{DS} = 0\text{ V to } 520\text{ V}, V_{GS} = 0\text{ V}$ | | - | 89 | - | μF |
| Effective Output Capacitance, Time Related ^b | $C_{o(tr)}$ | | | - | 307 | - | |
| Total Gate Charge | Q_g | $V_{GS} = 10\text{ V}$ | $I_D = 11\text{ A}, V_{DS} = 520\text{ V}$ | - | 73 | 110 | nC |
| Gate-Source Charge | Q_{gs} | | | - | 15 | - | |
| Gate-Drain Charge | Q_{gd} | | | - | 32 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 520\text{ V}, I_D = 11\text{ A}, V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$ | | - | 22 | 45 | ns |
| Rise Time | t_r | | | - | 33 | 66 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | - | 73 | 110 | |
| Fall Time | t_f | | | - | 38 | 76 | |
| Gate Input Resistance | R_g | $f = 1\text{ MHz}, \text{open drain}$ | | - | 0.64 | - | Ω |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous Source-Drain Diode Current | I_S | MOSFET symbol showing the integral reverse p - n junction diode  | | - | - | 22 | A |
| Pulsed Diode Forward Current | I_{SM} | | | - | - | 56 | |
| Diode Forward Voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}, I_S = 11\text{ A}, V_{GS} = 0\text{ V}$ | | - | - | 1.2 | V |
| Reverse Recovery Time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 11\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, V_R = 400\text{ V}$ | | - | 400 | - | ns |
| Reverse Recovery Charge | Q_{rr} | | | - | 5.9 | - | μC |
| Reverse Recovery Current | I_{RRM} | | | - | 20 | - | A |

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

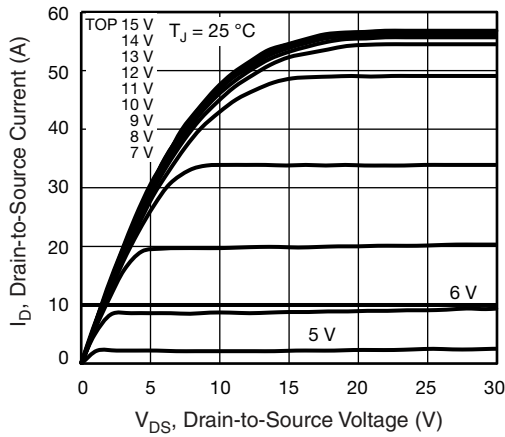


Fig. 1 - Typical Output Characteristics

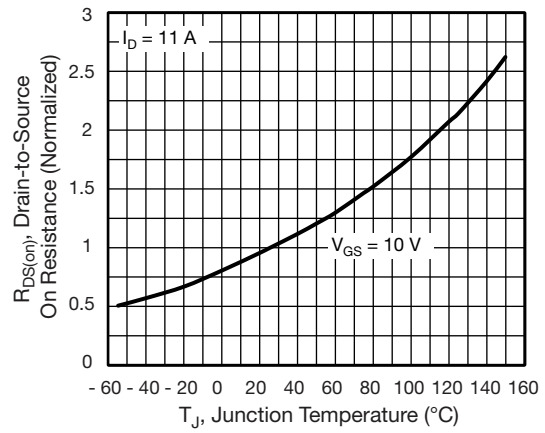


Fig. 4 - Normalized On-Resistance vs. Temperature

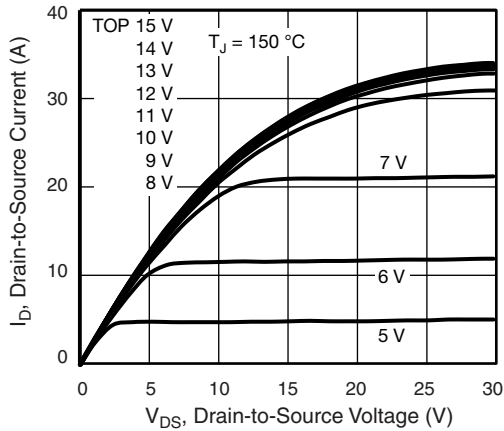


Fig. 2 - Typical Output Characteristics

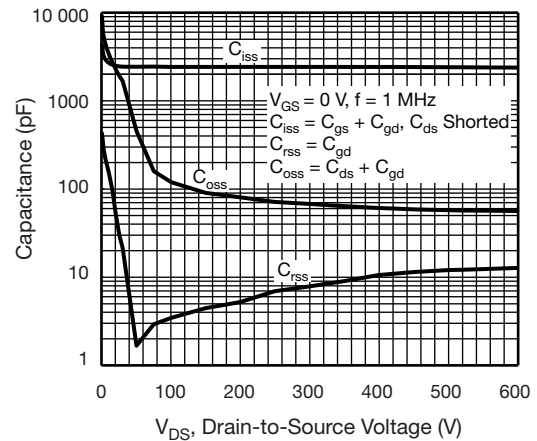


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

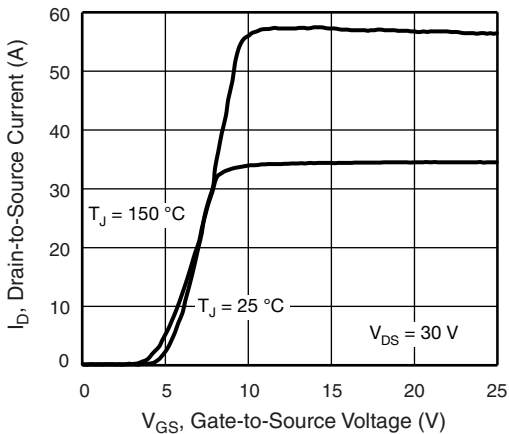


Fig. 3 - Typical Transfer Characteristics

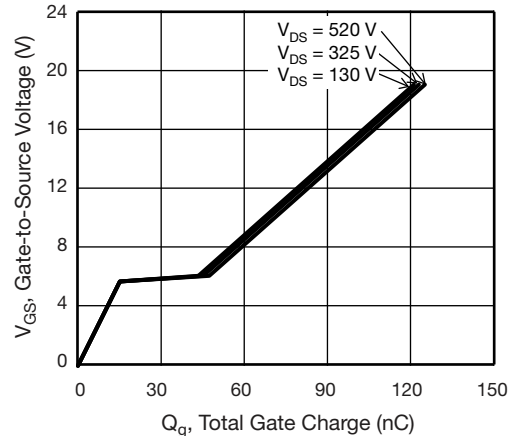


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

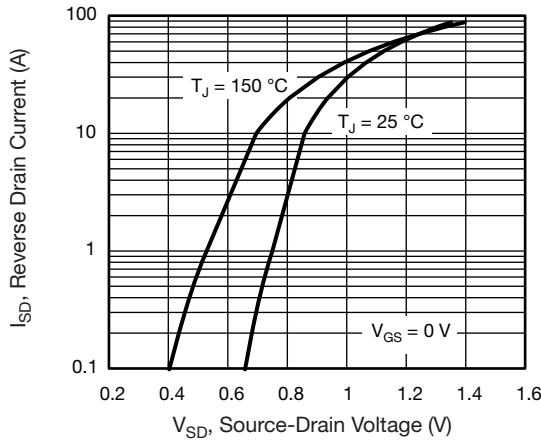


Fig. 7 - Typical Source-Drain Diode Forward Voltage

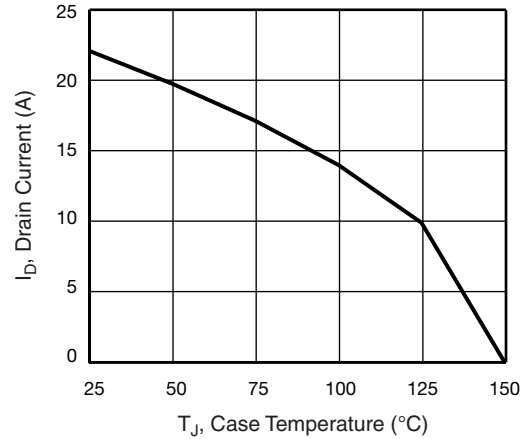


Fig. 9 - Maximum Drain Current vs. Case Temperature

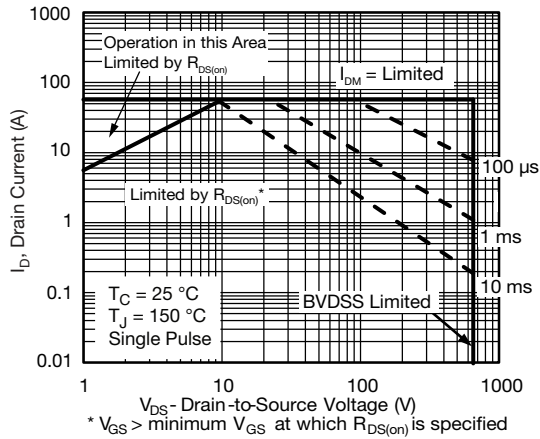


Fig. 8 - Maximum Safe Operating Area

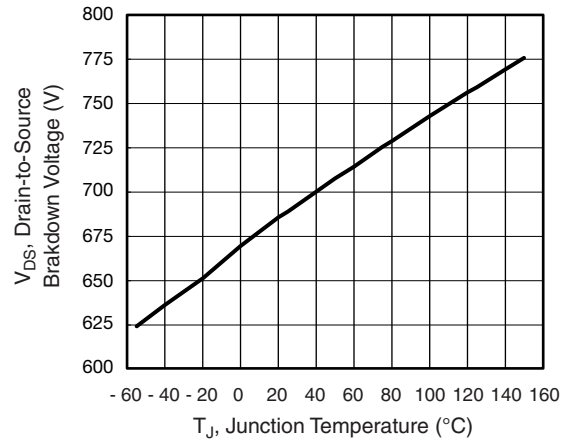


Fig. 10 - Temperature vs. Drain-to-Source Voltage

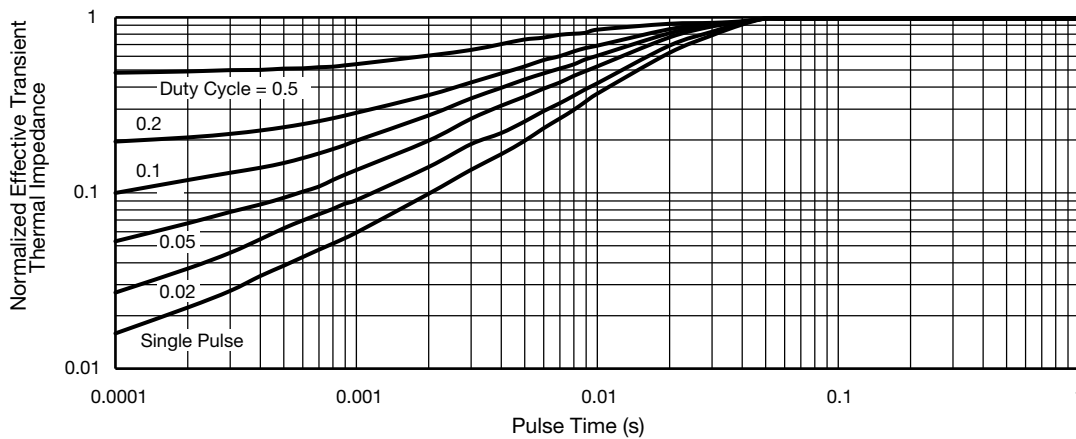


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

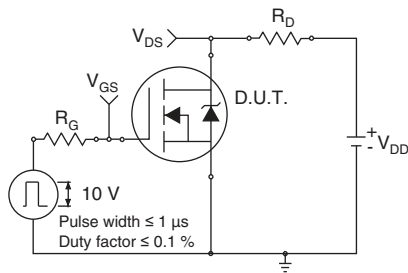


Fig. 12 - Switching Time Test Circuit

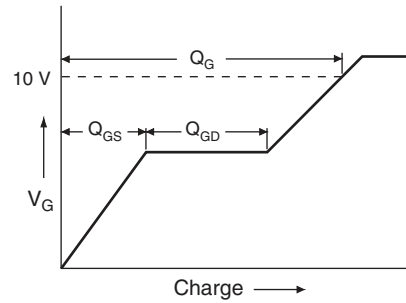


Fig. 16 - Basic Gate Charge Waveform

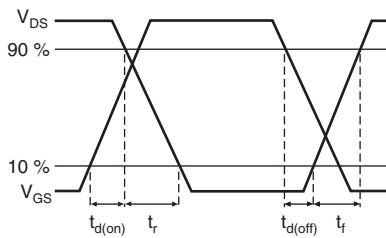


Fig. 13 - Switching Time Waveforms

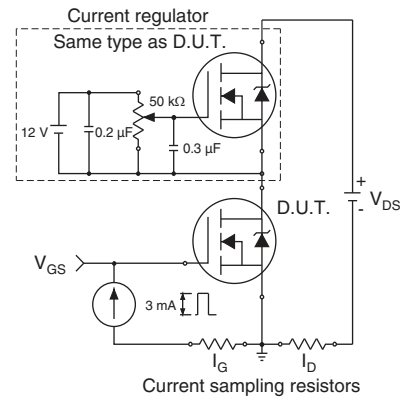


Fig. 17 - Gate Charge Test Circuit

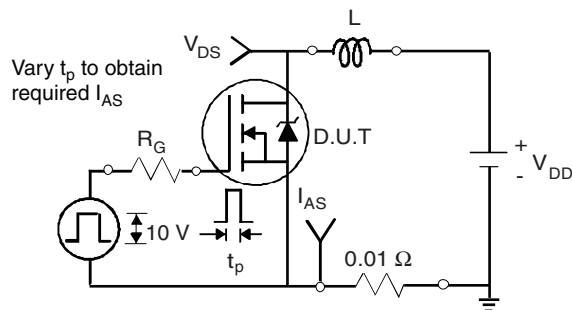


Fig. 14 - Unclamped Inductive Test Circuit

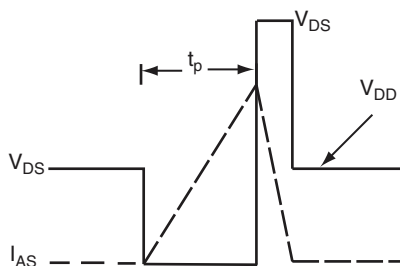
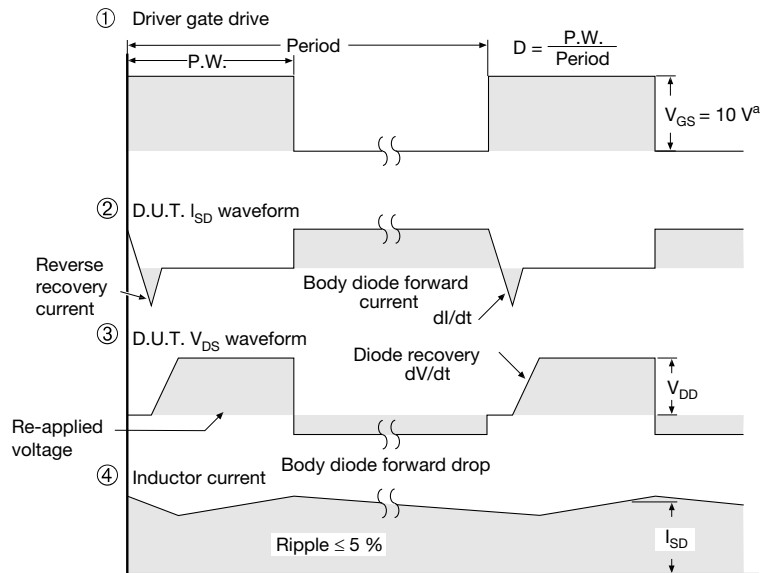
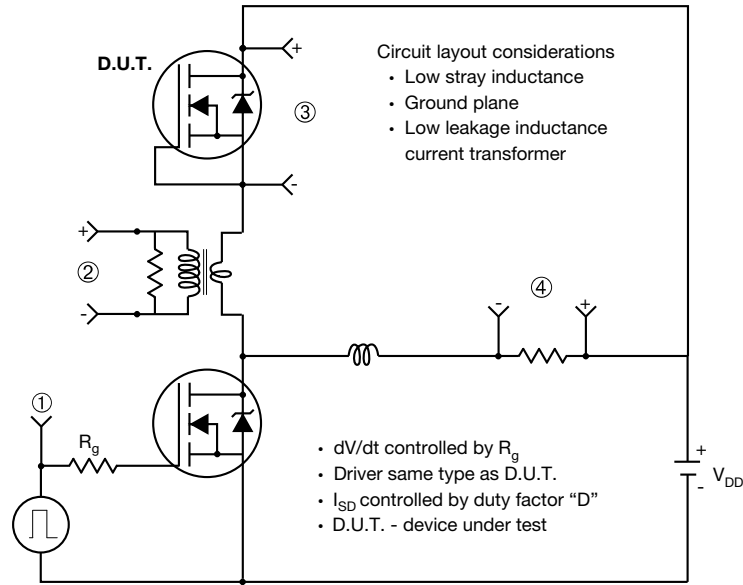


Fig. 15 - Unclamped Inductive Waveforms

Peak Diode Recovery dV/dt Test Circuit



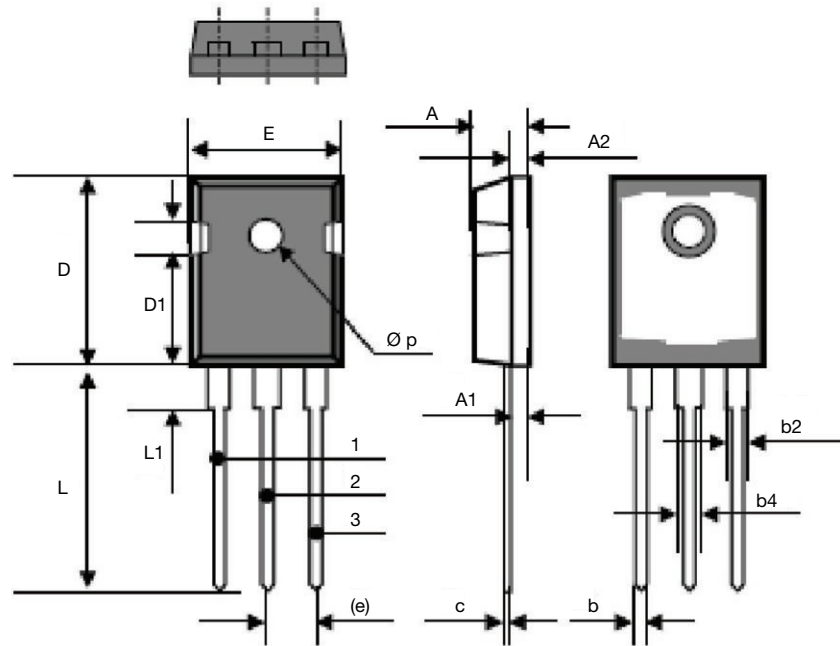
Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 18 - For N-Channel

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TO-247AD (High Voltage)



| DIM. | MILLIMETERS | | INCHES | |
|---------------------------------|-------------|-------|-----------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.70 | 5.31 | 0.185 | 0.209 |
| A1 | 2.21 | 2.59 | 0.087 | 0.102 |
| A2 | 1.50 | 2.49 | 0.059 | 0.098 |
| b | 0.99 | 1.40 | 0.039 | 0.055 |
| b2 | 1.65 | 2.41 | 0.065 | 0.095 |
| b4 | 2.59 | 3.43 | 0.102 | 0.135 |
| c | 0.61 BSC | | 0.024 BSC | |
| D | 20.80 | 21.46 | 0.819 | 0.845 |
| D1 | 3.68 | 5.49 | 0.145 | 0.216 |
| (e) | 5.46 BSC | | 0.215 BSC | |
| E | 15.49 | 16.26 | 0.610 | 0.640 |
| L | 19.81 | 20.32 | 0.780 | 0.800 |
| L1 | 4.06 | 4.50 | 0.160 | 0.177 |
| Ø p | 3.51 | 3.66 | 0.138 | 0.144 |
| ECN: S17-0178-Rev. B, 06-Feb-17 | | | | |
| DWG: 6010 | | | | |



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